

ABSTRACT

[0035] A metal oxide semiconductor field effect transistor (“MOSFET”) layout with small width-length ratio allows for greater flexibility in design and density in dimension than the conventional annular technique is provided. Accordingly, higher density MOSFET of this layout gives more devices on a single semiconductor wafer. An additional benefit of this layout is a reduced current density at the enclosed terminal wherein there is less localized heating and damages of materials composing the transistor.